

In The Claims:

1. An apparatus for etching stacks on a substrate, comprising:

a plasma chamber with chamber walls;

a plasma confinement device for reducing plasma contact with the chamber walls;

a gas source, comprising:

a fluorine containing gas source;

an ammonia containing gas source;

plasma generation and energizing device; and

an exhaust system for pumping plasma away.

Sub B1

A3

2. The apparatus, as recited in claim 1, further comprising a chuck for supporting the substrate within the plasma chamber, wherein the plasma confinement device confines the plasma adjacent to the substrate.

3. (Once Amended) The apparatus, as recited in claim 2, wherein a stack comprises a layer with a low dielectric constant material and an etch stop layer.

4. The apparatus, as recited in claim 3, wherein the plasma generation and energizing device comprises an upper electrode and a lower electrode spaced apart from the upper electrode.

5. The apparatus, as recited in claim 4, wherein the plasma confining device comprises a plurality of spaced apart plasma rings.

BEST AVAILABLE COPY

6. The apparatus, as recited in claim 5, wherein the upper electrode and lower electrode are spaced apart by a distance less than 2.0 cm.

7. The apparatus, as recited in claim 6, wherein the exhaust system is able to maintain a pressure below 300 mTorr within the chamber walls.

8. The apparatus, as recited in claim 1, wherein the plasma generation and energizing device comprises an upper electrode and a lower electrode spaced apart from the upper electrode.

9. The apparatus, as recited in claim 8, wherein the plasma confining device comprises a plurality of spaced apart plasma rings.

A3
Cet
10. The apparatus, as recited in claim 9, wherein the upper electrode and lower electrode are spaced apart by a distance less than 2.0 cm.

11. The apparatus, as recited in claim 10, wherein the exhaust system is able to maintain a pressure below 300 mTorr within the chamber walls.

12. The apparatus, as recited in claim 8, wherein the upper electrode and lower electrode are spaced apart by of distance less than 2.0 cm.

13. (Once Amended) The apparatus, as recited in claim 1, wherein the plasma confining device comprises a plurality of spaced apart plasma rings.

BEST AVAILABLE COPY

AB
14. (Once Amended) The apparatus, as recited in claim 13, wherein the exhaust system is able to maintain a pressure below 300 mTorr within the chamber walls.

15. (Once Amended) A method of etching a stack, comprising:

placing the stack in a plasma processing chamber;

flowing a fluorine containing gas into the plasma processing chamber;

flowing an ammonia containing gas into the plasma processing chamber;

generating a plasma; and

etching the stack.

16. (Once Amended) The method, as recited in claim 15, further comprising confining the plasma to reduce plasma contact with chamber walls.

A4
17. (Once Amended) The method, as recited in claim 15, wherein the stack comprises a low dielectric constant layer and an etch stop layer over a substrate.

18. (Once Amended) The method, as recited in claim 16, wherein the fluorine containing gas and the ammonia containing gas are provided in an alternating manner and wherein a plasma is generated from the fluorine containing gas and a plasma is generated from the ammonia containing gas.

A4
19. (New) The apparatus, as recited in claim 1, wherein the plasma confinement device is able to confine the plasma and prevent defects from the formation of particles from ammonia and fluorine.

DECT AVAIL ARLE COPY